BLF183XR; BLF183XRS

Power LDMOS transistor

Rev. 2 — 22 May 2015 Product data sheet

1. Product profile

1.1 General description

A 350 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 600 MHz band.

Table 1. Application information

Test signal	f	V_{DS}	P_L	G_p	η_D
	(MHz)	(V)	(W)	(dB)	(%)
pulsed RF	108	50	350	28	75
CW	88 to 108	50	388	26	80
pulsed RF	30 to 512	50	400	15	48
CW	30 to 512	35	193	14	47

1.2 Features and benefits

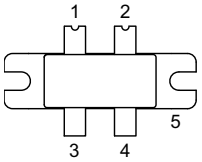
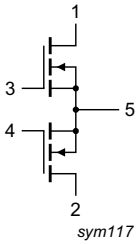
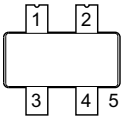
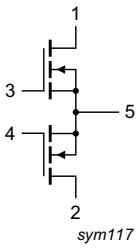
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 600 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF183XR (SOT1121A)			
1	drain1		
2	drain2		
3	gate1		
4	gate2		
5	source [1]		
BLF183XRS (SOT1121B)			
1	drain1		
2	drain2		
3	gate1		
4	gate2		
5	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF183XR	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1121A
BLF183XRS	-	earless flanged ceramic package; 4 leads	SOT1121B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	135	V
V_{GS}	gate-source voltage		−6	+11	V
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

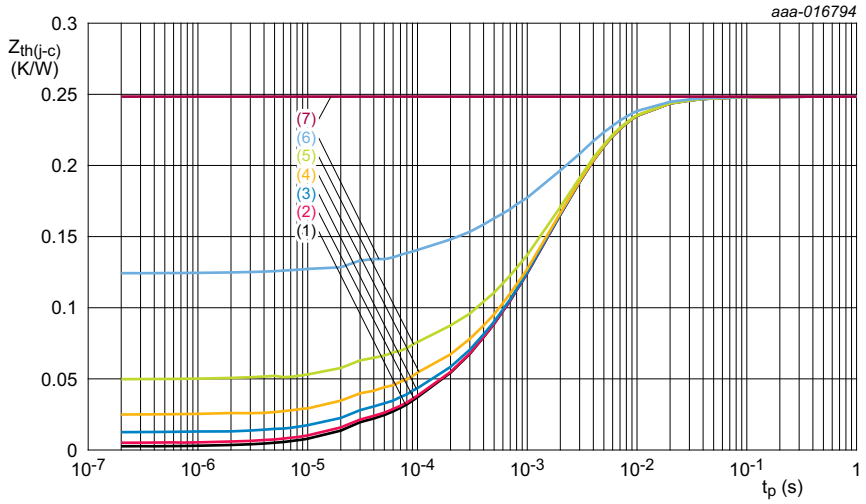
Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_j = 115 °C [1][2]	0.25	K/W
$Z_{th(j-c)}$	transient thermal impedance from junction to case	T_j = 150 °C; t_p = 100 μs; δ = 20 % [3]	0.076	K/W

[1] T_j is the junction temperature.

[2] $R_{th(j-c)}$ is measured under RF conditions.

[3] See Figure 1.



(1) δ = 1 %

(2) δ = 2 %

(3) δ = 5 %

(4) δ = 10 %

(5) δ = 20 %

(6) δ = 50 %

(7) δ = 100 % (DC)

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

T_j = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 1.5 mA	135	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 150 mA	1.33	2.0	2.33	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 50 V; I_D = 50 mA	-	1.9	-	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 50 V	-	-	1.4	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	21	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 5.25 A	-	0.29	-	Ω

Table 7. AC characteristics

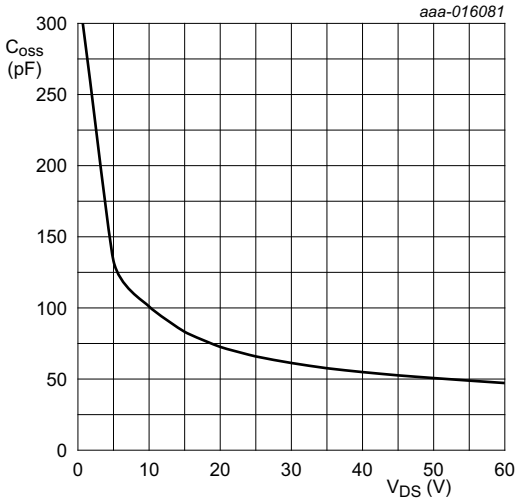
T_j = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{rs}	feedback capacitance	V_{GS} = 0 V; V_{DS} = 50 V; f = 1 MHz	-	1.1	-	pF
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 50 V; f = 1 MHz	-	156	-	pF
C_{oss}	output capacitance	V_{GS} = 0 V; V_{DS} = 50 V; f = 1 MHz	-	51	-	pF

Table 8. RF characteristics

Test signal: pulsed RF; t_p = 100 µs; δ = 20 %; f = 108 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 100 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	P_L = 350 W	26.5	28	-	dB
RL_{in}	input return loss	P_L = 350 W	-	−10	−7	dB
η_D	drain efficiency	P_L = 350 W	71	75	-	%



V_{GS} = 0 V; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

7. Test information

7.1 Ruggedness in class-AB operation

The BLF183XR and BLF183XRS are capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 100 mA; P_L = 350 W pulsed; f = 108 MHz.

7.2 Impedance information

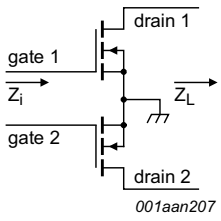


Fig 3. Definition of transistor impedance

Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at V_{DS} = 50 V and P_L = 350 W.

f	Z_i	Z_L
(MHz)	**(Ω)**	**(Ω)**
108	10.3 – j35.6	10.9 + j2.5

7.3 UIS avalanche energy

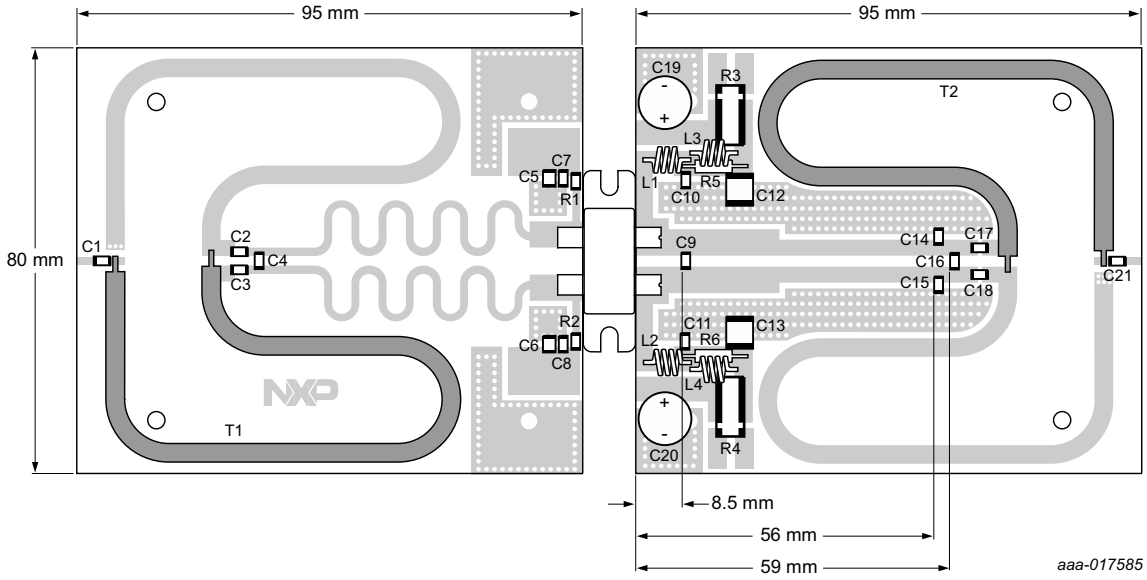
Table 10. Typical avalanche data per section

T_{amb} = 25 °C; typical test data; test jig without water cooling.

I_{AS}	E_{AS}
(A)	**(J)**
10	2.6
12.5	1.5
15	1.0

For information see application note *AN10273*.

7.4 Test circuit



Printed-Circuit Board (PCB): Taconic RF-35; ε_r = 3.5 F/m; thickness = 0.765 mm; thickness copper plating = 35 μm, gold plated.

See Table 11 for a list of components.

Fig 4. Component layout for class-AB production test circuit

Table 11. List of components

For test circuit see Figure 4.

Component	Description	Value	Remarks
C1, C4	multilayer ceramic chip capacitor	51 pF [1]	
C2, C3	multilayer ceramic chip capacitor	150 pF [1]	
C5, C6	multilayer ceramic chip capacitor	4.7 μF, 50 V	
C7, C8	multilayer ceramic chip capacitor	820 pF [1]	
C9	multilayer ceramic chip capacitor	11 pF [1]	
C10, C11	multilayer ceramic chip capacitor	820 pF [1]	
C12, C13	multilayer ceramic chip capacitor	4.7 μF, 100 V	
C14, C15, C21	electrolytic capacitor	51 pF [1]	

Table 11. List of components *...continued*

For test circuit see Figure 4.

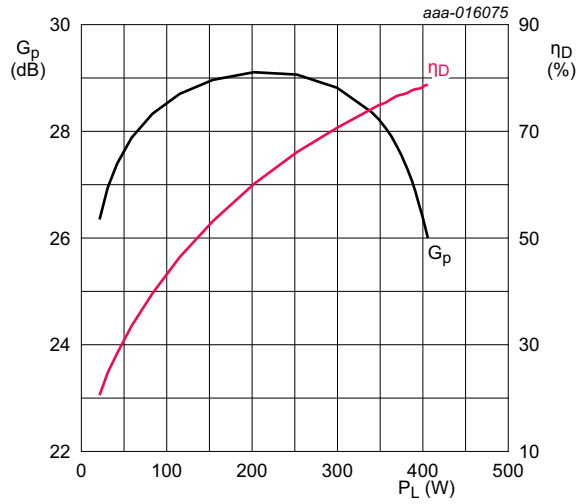
Component	Description	Value	Remarks
C16	multilayer ceramic chip capacitor	7.5 pF [1]	
C17,C18	multilayer ceramic chip capacitor	120 pF [1]	
C19, C20	electrolytic capacitor	2200 μF, 64 V	
L1, L2, L3, L4	3.0 turn 1.0 mm copper wire	D = 3.0 mm	
R1, R2	resistor	510 Ω	SMD 1206
R3, R4	shunt resistor	0.01 Ω	Ohmite: FC4L110R010FER
R5, R6	metal film resistor	10 Ω, 0.6 W	SMD 1206
T1, T2	semi rigid coax	50 Ω, length = 160 mm	EZ Form: EZ-141-AL-TP-M17

[1] American Technical Ceramics type 100B or capacitor of same quality.

7.5 Graphical data

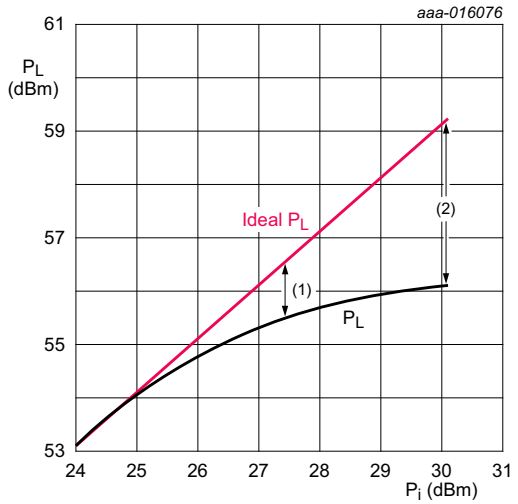
The following figures are measured in a class-AB production test circuit.

7.5.1 1-Tone CW pulsed



V_{DS} = 50 V; I_{Dq} = 100 mA; f = 108 MHz; t_p = 100 μs; δ = 20 %.

Fig 5. Power gain and drain efficiency as function of output power; typical values

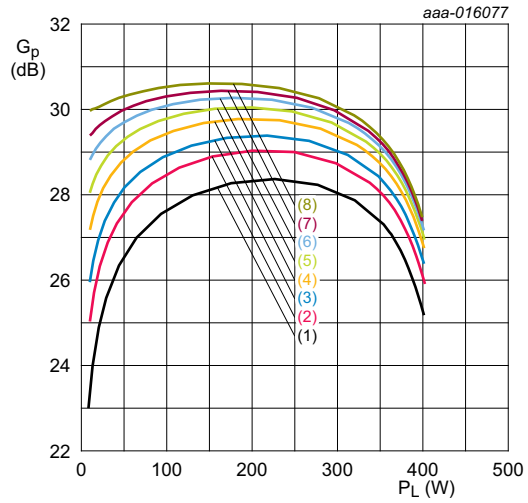


V_{DS} = 50 V; I_{Dq} = 100 mA; f = 108 MHz; t_p = 100 μs; δ = 20 %.

(1) $P_{L(1dB)}$ = 55.5 dBm (354 W)

(2) $P_{L(3dB)}$ = 56.1 dBm (404 W)

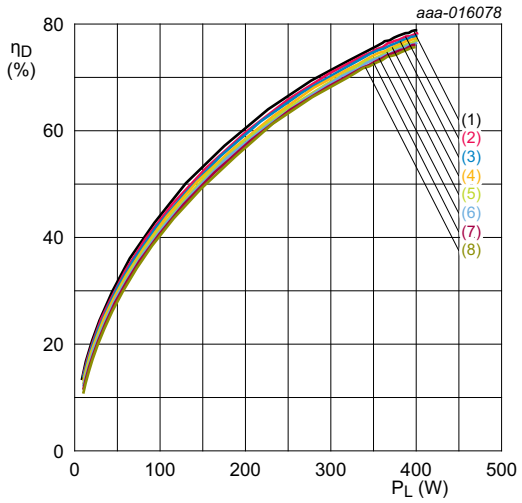
Fig 6. Output power as a function of input power; typical values



V_{DS} = 50 V; f = 108 MHz; t_p = 100 µs; δ = 20 %.

(1) I_{Dq} = 20 mA
(2) I_{Dq} = 100 mA
(3) I_{Dq} = 200 mA
(4) I_{Dq} = 400 mA
(5) I_{Dq} = 600 mA
(6) I_{Dq} = 800 mA
(7) I_{Dq} = 1000 mA
(8) I_{Dq} = 1200 mA

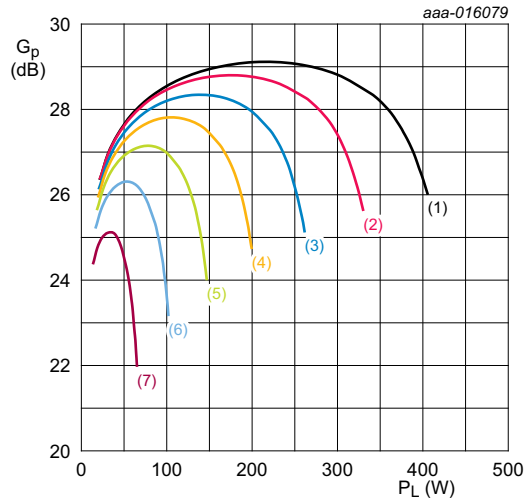
Fig 7. Power gain as a function of output power; typical values



V_{DS} = 50 V; f = 108 MHz; t_p = 100 µs; δ = 20 %.

(1) I_{Dq} = 20 mA
(2) I_{Dq} = 100 mA
(3) I_{Dq} = 200 mA
(4) I_{Dq} = 400 mA
(5) I_{Dq} = 600 mA
(6) I_{Dq} = 800 mA
(7) I_{Dq} = 1000 mA
(8) I_{Dq} = 1200 mA

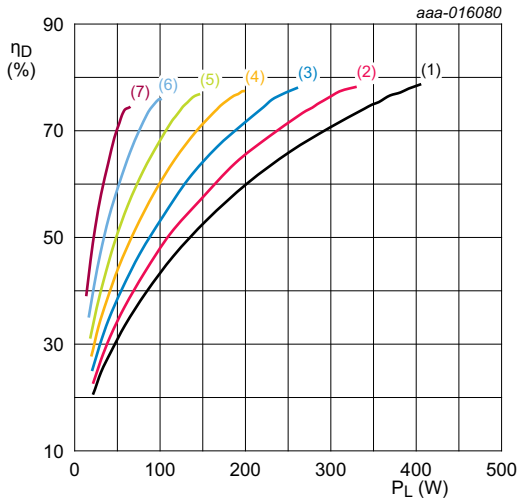
Fig 8. Drain efficiency as a function of output power; typical values



I_{Dq} = 100 mA; f = 108 MHz; t_p = 100 μs; δ = 20 %.

(1) V_{DS} = 50 V
(2) V_{DS} = 45 V
(3) V_{DS} = 40 V
(4) V_{DS} = 35 V
(5) V_{DS} = 30 V
(6) V_{DS} = 25 V
(7) V_{DS} = 20 V

Fig 9. Power gain as a function of output power; typical values



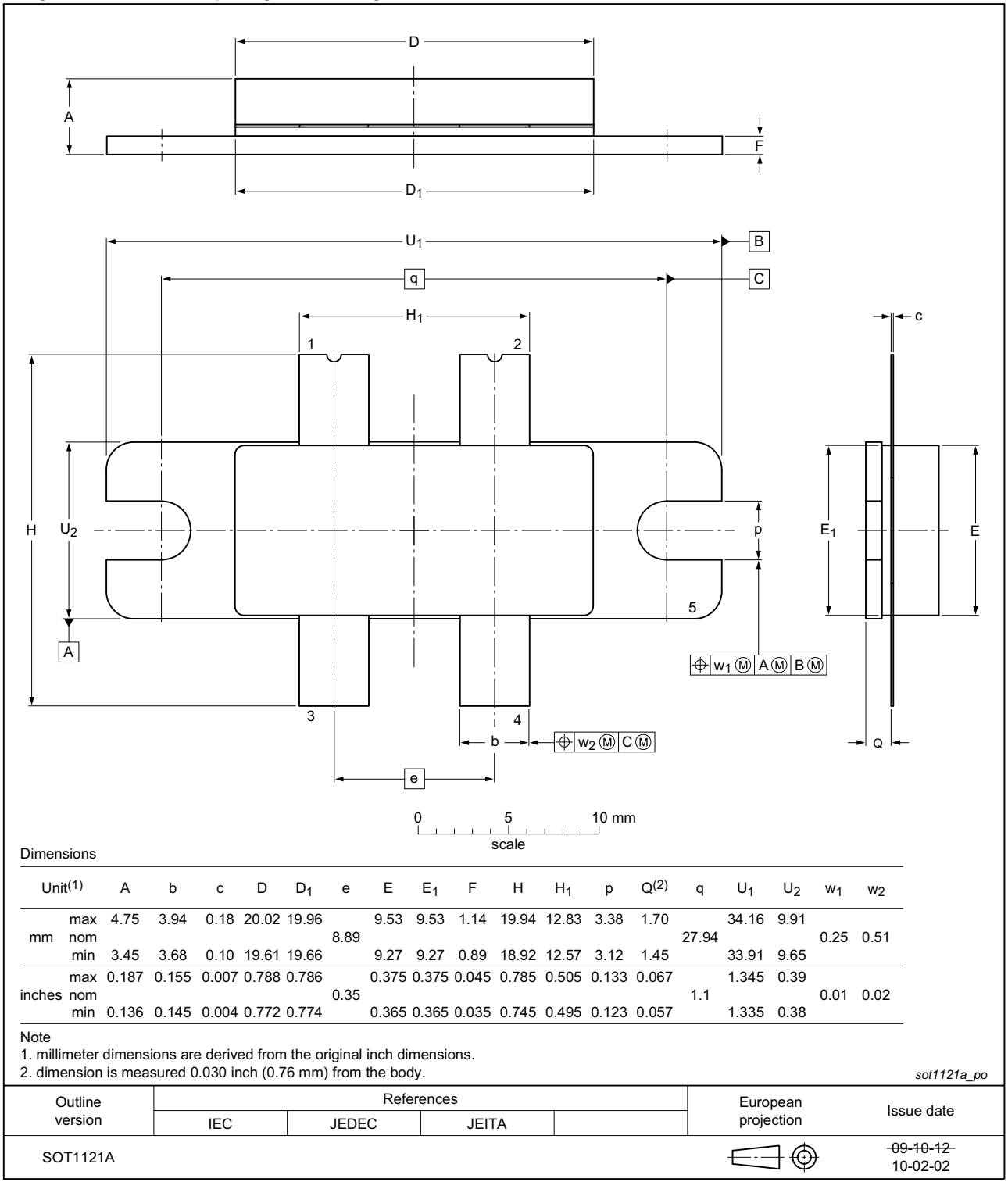
I_{Dq} = 100 mA; f = 108 MHz; t_p = 100 μs; δ = 20 %.

(1) V_{DS} = 50 V
(2) V_{DS} = 45 V
(3) V_{DS} = 40 V
(4) V_{DS} = 35 V
(5) V_{DS} = 30 V
(6) V_{DS} = 25 V
(7) V_{DS} = 20 V

Fig 10. Drain efficiency as a function of output power; typical values

8. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 4 leads **SOT1121A**



Dimensions

Unit(1)		A	b	c	D	D_1	e	E	E_1	F	H	H_1	p	Q(2)	q	U_1	U_2	w_1	w_2
mm	max	4.75	3.94	0.18	20.02	19.96		9.53	9.53	1.14	19.94	12.83	3.38	1.70		34.16	9.91		
	nom						8.89								27.94			0.25	0.51
	min	3.45	3.68	0.10	19.61	19.66		9.27	9.27	0.89	18.92	12.57	3.12	1.45		33.91	9.65		
inches	max	0.187	0.155	0.007	0.788	0.786		0.375	0.375	0.045	0.785	0.505	0.133	0.067		1.345	0.39		
	nom						0.35								1.1			0.01	0.02
	min	0.136	0.145	0.004	0.772	0.774		0.365	0.365	0.035	0.745	0.495	0.123	0.057		1.335	0.38		

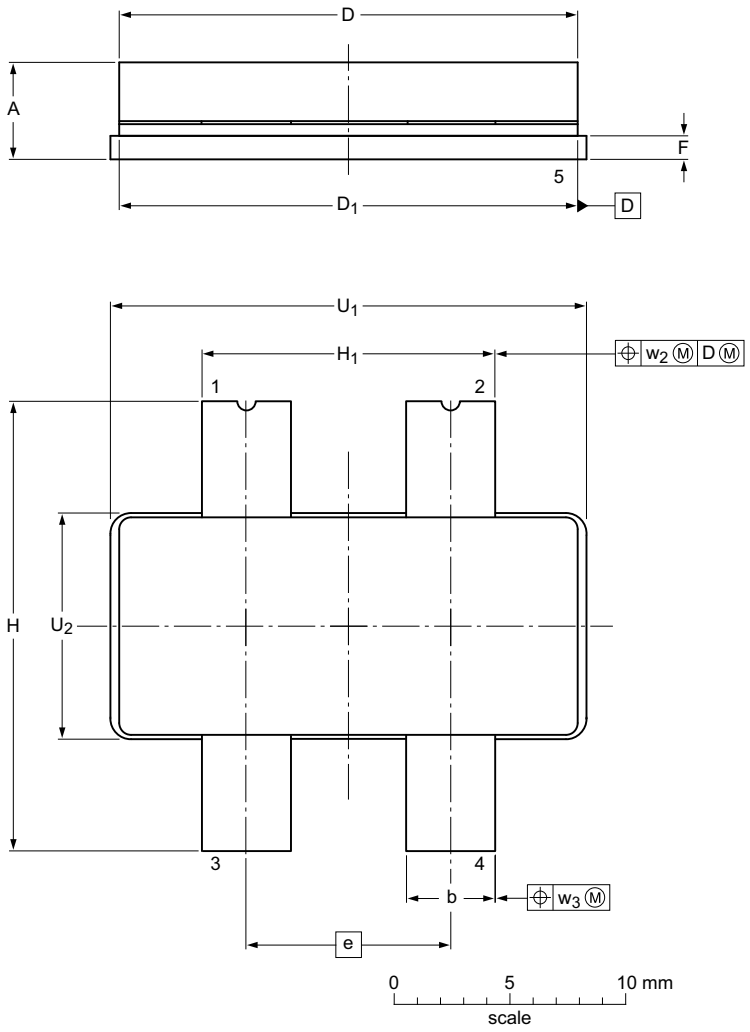
Note
1. millimeter dimensions are derived from the original inch dimensions.
2. dimension is measured 0.030 inch (0.76 mm) from the body.

sot1121a_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1121A						~~09-10-12~~ 10-02-02

Fig 11. Package outline SOT1121A

Earless flanged ceramic package; 4 leads **SOT1121B**



Dimensions

Unit[1]		A	b	c	D	D_1	e	E	E_1	F	H	H_1	Q	U_1	U_2	w_2	w_3	y
mm	max	4.75	3.94	0.18	20.02	19.96		9.53	9.53	1.14	19.94	12.83	1.70	20.70	9.91	0.51	0.25	0.25
	nom						8.89											
	min	3.45	3.68	0.08	19.61	19.66		9.27	9.27	0.89	18.92	12.57	1.45	20.45	9.65			
inches	max	0.187	0.155	0.007	0.788	0.786		0.375	0.375	0.045	0.785	0.505	0.067	0.815	0.39	0.02	0.01	0.01
	nom						0.35											
	min	0.136	0.145	0.003	0.772	0.774		0.365	0.365	0.035	0.745	0.495	0.057	0.805	0.38			

Note
1. millimeter dimensions are derived from the original inch dimensions.
2. dimension is measured 0.030 inch (0.76 mm) from the body.

sot1121b_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1121B						~~09-12-14~~ 12-06-07

Fig 12. Package outline SOT1121B

9. Handling information

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
MTF	Median Time to Failure
SMD	Surface Mounted Device
UIS	Unclamped Inductive Switching
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF183XR_BLF183XRS v.2	20150522	Product data sheet	-	BLF183XR_BLF183XRS v.1
Modifications:	• Table 1 on page 1; table updated • Table 5 on page 3; table updated • Table 6 on page 4; table updated • Figure 1 on page 3; figure added • Table 7 on page 4; table updated • Table 8 on page 4; table updated • Figure 2 on page 5; figure added • Table 10 on page 6; table updated • Section 7.4 on page 6; section added • Section 7.5 on page 7; section added			
BLF183XR_BLF183XRS v.1	20140819	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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13. Contact information

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